



SINGLE N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	30mΩ @ V _{GS} = 10V	7.1A
30V	40mΩ @ V _{GS} = 4.5V	6.2A
	63mΩ @ V _{GS} = 2.5V	4.9A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features and Benefits

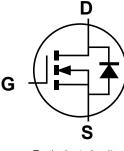
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)



SL	0	
s 🗖		□D
s 🗖		□D
G□		ΠD
	Top View Internal Schematic	



Equivalent circuit

Ordering Information (Note 4)

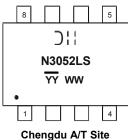
Part Number	Case	Packaging
DMN3052LSS-13	SO-8	2500/Tape & Reel

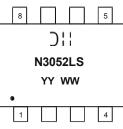
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. Notes:

2. See http://www.diodes.com/guality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Shanghai A/T Site

) | | = Manufacturer's Marking N3052LS = Product Type Marking Code YYWW = Date Code Marking YY or \overline{YY} = Year (ex: 13 = 2013) WW = Week (01 - 53) YY = Date Code Marking for SAT (Shanghai Assembly/ Test site) YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±12	V
Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +70°C	I _D	7.1 5.7	А
Pulsed Drain Current (Note 6)			I _{DM}	28	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	PD	2.5	W	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ ext{ heta}JA}$	50	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

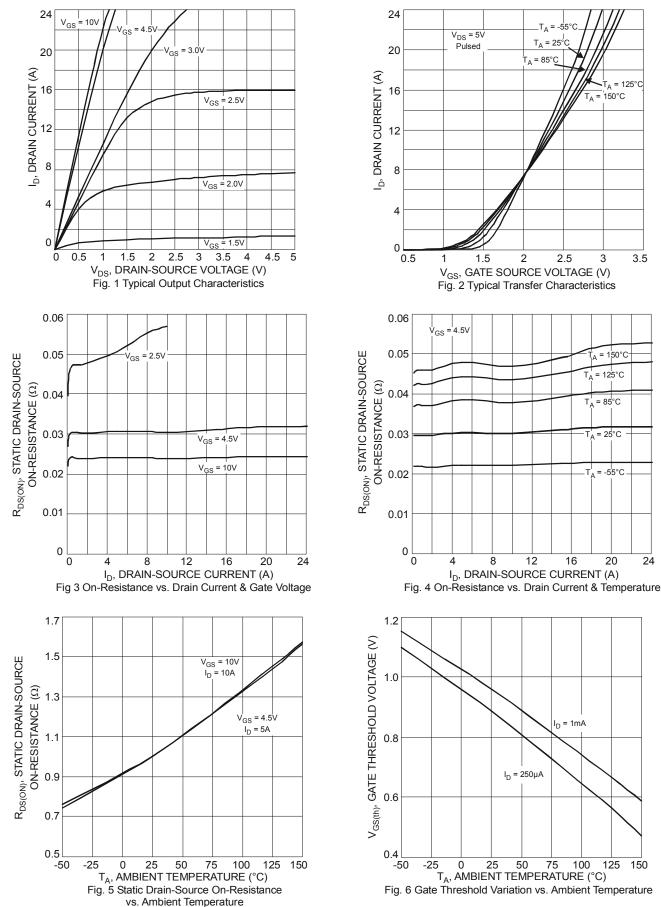
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						-
Drain-Source Breakdown Voltage	BV _{DSS}	30			V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	_		1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}			±80 ±800	nA	V_{GS} = ±12V, V_{DS} = 0V V_{GS} = ±19V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)					_	
Gate Threshold Voltage	V _{GS(th)}	0.62	0.9	1.2	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS (ON)}	_	24 30 50	30 40 63	mΩ	V_{GS} = 10V, I _D = 7.1A V_{GS} = 4.5V, I _D = 6.4A V_{GS} = 2.5V, I _D = 5.0A
Forward Transconductance	g fs	_	10		S	V _{DS} = 5V, I _D = 5.1A
Diode Forward Voltage (Note 7)	V _{SD}	_	0.78	1.16	V	V _{GS} = 0V, I _S = 2.1A
DYNAMIC CHARACTERISTICS						-
Input Capacitance	Ciss	_	555		pF	
Output Capacitance	Coss	_	109		pF	V _{DS} = 5V, V _{GS} = 0V - f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	82		pF	

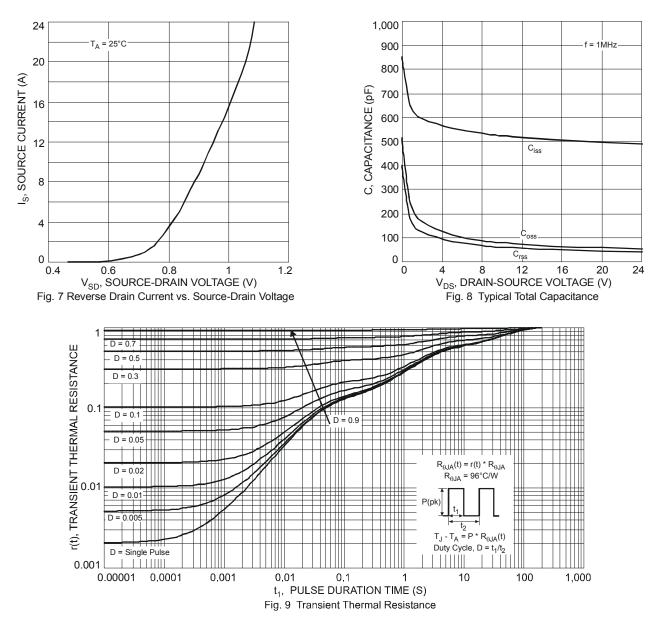
 $\begin{array}{lll} \mbox{Notes:} & 5. & \mbox{Device mounted on 2 oz copper pad layout with R_{0JA} = $50^{\circ}C/W$.} \\ & 6. & \mbox{Pulse width \le10\mu$S, Duty Cycle \le1\%$.} \\ & 7. & \mbox{Short duration pulse test used to minimize self-heating effect.} \end{array}$



DMN3052LSS

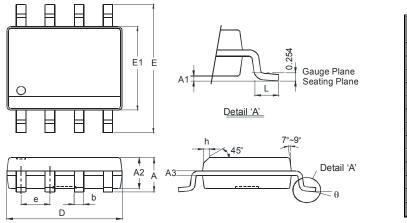






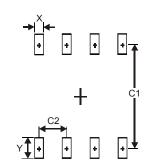


Package Outline Dimensions



SO-8					
Dim	Min	Max			
Α	-	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85 3.95				
е	1.27 Typ				
h	- 0.35				
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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